

Marked-up copy of the claims as amended:

**IN THE CLAIMS:**

Please amend the claims as follows:

9. (Amended) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming an anode on the second insulating film; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

10. (Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the surface of the anode is made flat by the wiping and cleaning material.

11. (No Amendment) The process for producing the active matrix type light emitting device according to claim 8, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

12. (No Amendment) The process for producing the active matrix type light emitting device according to claim 8, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

13. (Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the wiping and cleaning material is a PVA-based porous body.

14. (Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the anode is wiped and cleaned with the wiping and cleaning material and a washing liquid.

15. (Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

16. (Amended) The process for producing the active matrix type light emitting device according to claim 8, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

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Please add the following new claims:

38. (New) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming a transparent conductive film formed on the second insulating film;

patterning the transparent conductive film to form an anode; and

wiping and cleaning the surface of the anode with a wiping and cleaning material.

39. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein the surface of the anode is made flat by the wiping and cleaning material.

40. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

41. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

42. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein the wiping and cleaning material is a PVA-based porous body.

43. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein the anode is wiped and cleaned with the wiping and cleaning material and a washing liquid.

44. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

45. (New) The process for producing the active matrix type light emitting device according to claim 38, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

46. (New) A process for producing an active matrix light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic material on the first insulating film;

forming an electrode connected to the thin film transistor on the second insulating film;

forming an anode formed on the electrode and the second insulating film; and wiping and cleaning the surface of the anode with a wiping and cleaning material.

47. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein the surface of the anode is made flat by the wiping and cleaning material.

48. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

49. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

50. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein the wiping and cleaning material is a PVA-based porous body.

51. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

52. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

53. (New) The process for producing the active matrix type light emitting device according to claim 46, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

54. (New) A process for producing an active matrix type light emitting device comprising the steps of:

forming a thin film transistor over a substrate;

forming a first insulating film comprising organic resin material over the thin film transistor;

forming a second insulating film comprising inorganic insulating material on the first insulating film;

forming an anode on the second insulating film;

wiping and cleaning the surface of the anode with a wiping and cleaning material; and

forming an organic compound layer on the wiped and cleaned surface of the anode.

55. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein the surface of the anode is made flat by the wiping and cleaning material.

56. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

57. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

58. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein the wiping and cleaning material is a PVA-based porous body.

59. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein the anode is wiped and cleaned with the wiping and cleaning material and a washing liquid.

60. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

61. (New) The process for producing the active matrix type light emitting device according to claim 54, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

62. (New) A process for producing an active matrix type light emitting device comprising the steps of:

- forming a thin film transistor over a substrate;
- forming a first insulating film over the thin film transistor;
- forming a second insulating film on the first insulating film;
- forming an anode on the second insulating film; and
- wiping and cleaning the surface of the anode with a wiping and cleaning material.

63. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein the surface of the anode is made flat by the wiping and cleaning material.

64. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

65. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

66. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein the wiping and cleaning material is a PVA-based porous body.

67. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein the anode is wiping and cleaning with the wiping and cleaning material and a washing liquid.

68. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein the surface of the anode is scrubbed with the wiping and cleaning material.

69. (New) The process for producing the active matrix type light emitting device according to claim 62, wherein when contact angle to the surface of the anode is smaller than 90° before the wiping and cleaning, the contact angle after the wiping and cleaning is larger than the contact angle before the wiping and cleaning and is smaller than 90°.

70. (New) A process for producing an active matrix type light emitting device comprising the steps of:

- forming a thin film transistor over a substrate;
- forming a first insulating film over the thin film transistor;
- forming a second insulating film on the first insulating film;

forming an anode on the second insulating film;  
wiping and cleaning the surface of the anode with a wiping and cleaning material; and

forming an organic compound layer on the wiped and cleaned surface of the anode.

71. (New) The process for producing the active matrix type light emitting device according to claim 70, wherein the surface of the anode is made flat by the wiping and cleaning material.

72. (New) The process for producing the active matrix type light emitting device according to claim 70, wherein the organic resin material is selected from the group consisting of polyacrylate, polyimide and polyamide.

73. (New) The process for producing the active matrix type light emitting device according to claim 70, wherein the inorganic insulating material is selected from the group consisting of silicon oxide, silicon nitride, silicon oxide nitride, silicon nitride oxide, aluminum nitride, aluminum nitride oxide and aluminum oxide nitride.

74. (New) The process for producing the active matrix type light emitting device according to claim 70, wherein the wiping and cleaning material is a PVA-based porous body.

75. (New) The process for producing the active matrix type light emitting device according to claim 70, wherein the anode is wiped and cleaned with the wiping and cleaning material and a washing liquid.

76. (New) The process for producing the active matrix type light emitting device according to claim 70, wherein the surface of the anode is scrubbed with the wiping and cleaning material.